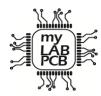




## Bill of Materials

Designator	Description	Value	Q
C1	Electrolytic capacitor 16v/50v	10µF	1
C2, C3, C4, C5, C6,	Ceramic or tantalum capacitor	100nF	7
IC1, IC2, IC4	4-Bits 2-Line to 1 Line data selector	74LS157	3
IC3	Non inverting bus transceiver	74LS245	1
IC5	Quad 2-input NAND gates	74LS00	1
MEM1, MEM2	SRAM 16x8 bits, not inverted outputs	74LS219	2
P1	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 16	16p	1
P2	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 32	32p	1
P4	Socket Header, THT, pitch 2.54mm, Dual Row, Vertical,	24p	1
P5	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 8p	8p	1
R1	Resistor Axial	1K	1
R2	Resistor Axial	4.7K	1
RN1	Resistor array 8 elements, 9 pins	330Ω	1
SW1	DIP switch 8 positions	8 pos	1
SW2	Mini slide switch 2 pos, 3 pins		1
SW3	Tactile button 6 mm	6mm	1



## Assembly List

Designator	Description	Value
C1	Electrolytic capacitor 16v/50v	10µF
C2	Ceramic or tantalum capacitor	100nF
C3	Ceramic or tantalum capacitor	100nF
C4	Ceramic or tantalum capacitor	100nF
C5	Ceramic or tantalum capacitor	100nF
C6	Ceramic or tantalum capacitor	100nF
C7	Ceramic or tantalum capacitor	100nF
C8	Ceramic or tantalum capacitor	100nF
IC1	4-Bits 2-Line to 1 Line data selector	74LS157
IC2	4-Bits 2-Line to 1 Line data selector	74LS157
IC3	Non inverting bus transceiver	74LS245
IC4	4-Bits 2-Line to 1 Line data selector	74LS157
IC5	Quad 2-input NAND gates	74LS00
MEM1	SRAM 16x8 bits, not inverted outputs	74LS219
MEM2	SRAM 16x8 bits, not inverted outputs	74LS219
P1	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 16p	16p
P2	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 32p	32p
P4	Socket Header, THT, pitch 2.54mm, Dual Row, Vertical, 24r	24p
P5	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 8p	8p
R1	Resistor Axial	1K
R2	Resistor Axial	4.7K
RN1	Resistor array 8 elements,9 pins	330Ω
SW1	DIP switch 8 positions	8 pos
SW2	Mini slide switch 2 pos, 3 pins	
SW3	Tactile button 6 mm	6mm